

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_C = +25^\circ C$
-60V	50mΩ @ $V_{GS} = -10V$	-18A
	70mΩ @ $V_{GS} = -4.5V$	-15A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

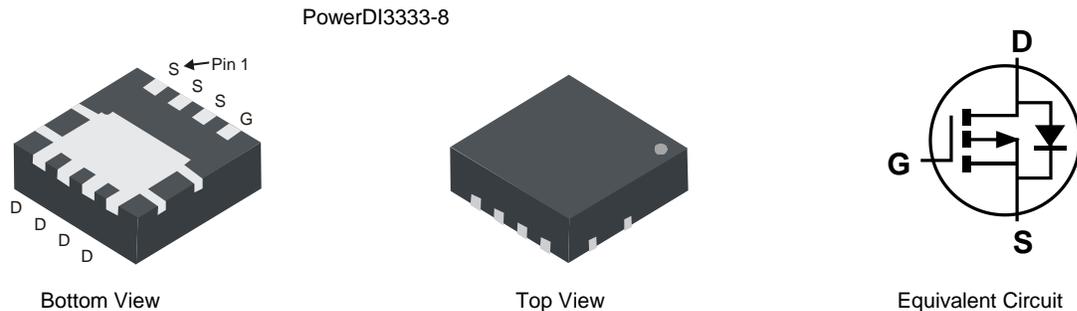
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low  $R_{DS(ON)}$  – ensures on state losses are minimized
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: PowerDI<sup>®</sup> 3333-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)

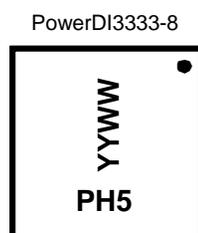


## Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH6050SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMPH6050SFGQ-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



PH5= Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Two Digits of Year (ex: 17 = 2017)  
WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-6.1	A
		T <sub>A</sub> = +100°C		-4.2	
Continuous Drain Current (Note 8) V <sub>GS</sub> = -10V	Steady State	T <sub>C</sub> = +25°C	I <sub>D</sub>	-18	A
		T <sub>C</sub> = +100°C		-12	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-32	A
Maximum Continuous Body Diode Forward Current (Note 7)			I <sub>S</sub>	-2	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-32	A
Avalanche Current (Note 9) L = 0.1mH			I <sub>AS</sub>	-24.8	A
Avalanche Energy (Note 9) L = 0.1mH			E <sub>AS</sub>	30.8	mJ

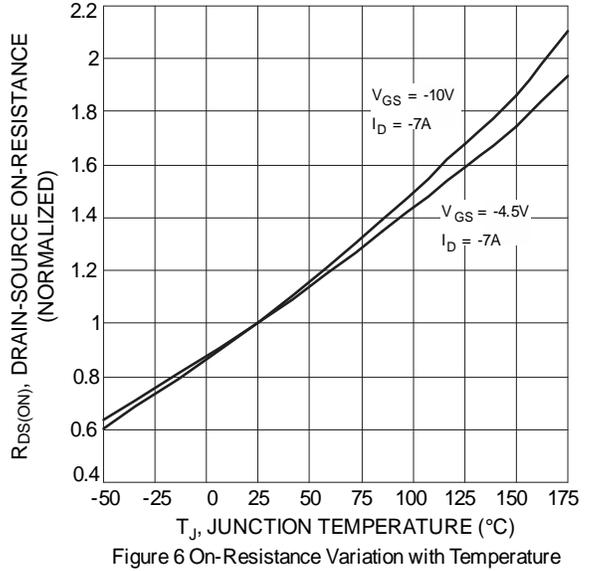
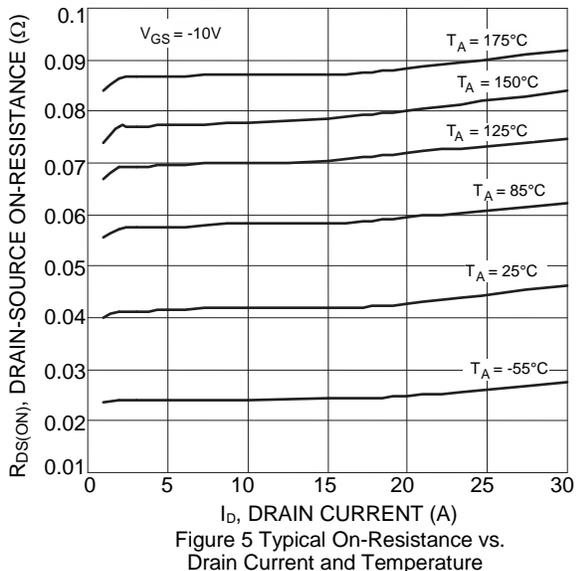
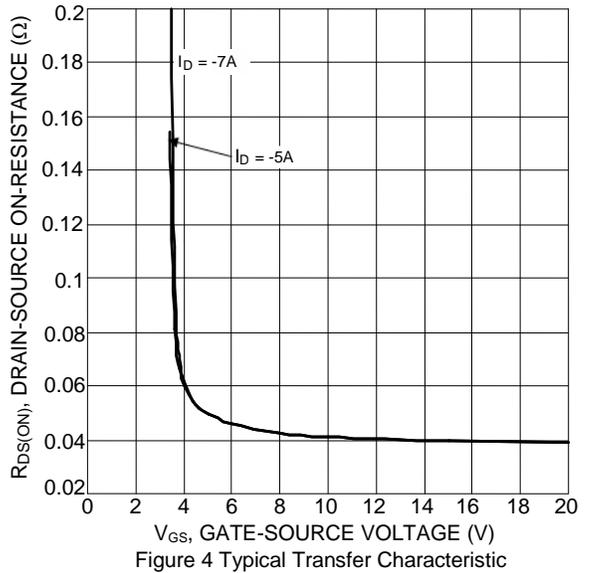
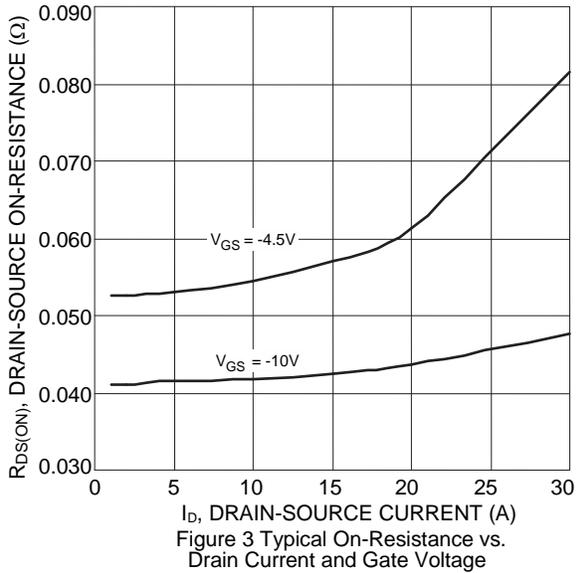
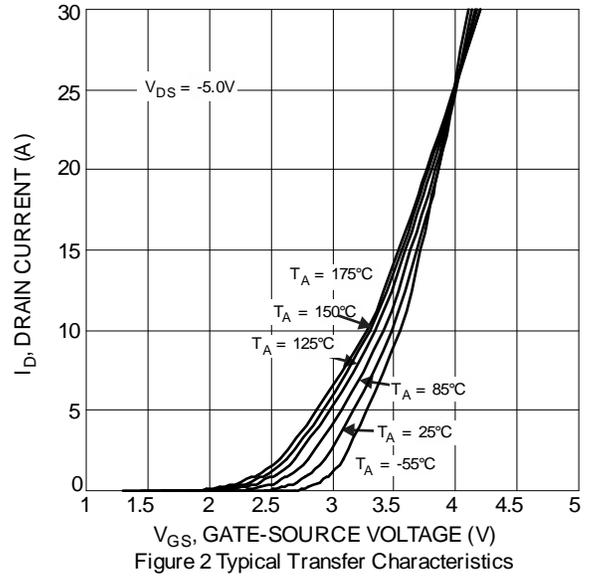
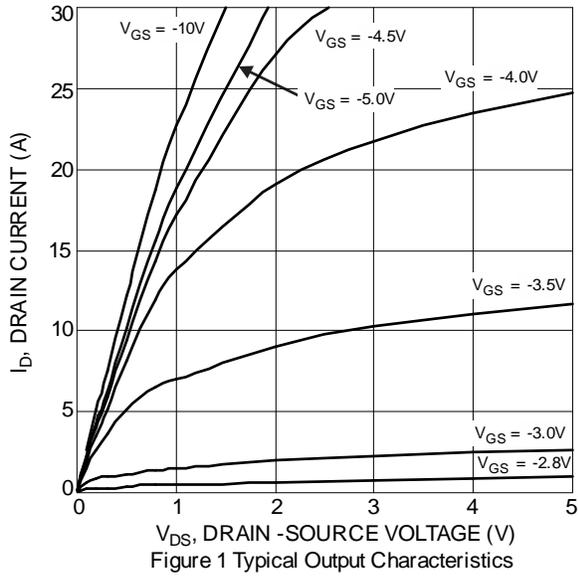
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R <sub>θJA</sub>	125	°C/W
	t < 10s		85	
Total Power Dissipation (Note 7)		P <sub>D</sub>	2.8	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	R <sub>θJA</sub>	54	°C/W
	t < 10s		37	
Thermal Resistance, Junction to Case (Note 8)		R <sub>θJC</sub>	6	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 10)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 10)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	41	50	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -7A
		—	52	70		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -7A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 11)</b>						
Input Capacitance	C <sub>iSS</sub>	—	1293	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	86.3	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	64.7	—	pF	
Gate Resistance	R <sub>g</sub>	—	12	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	11.9	—	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	24.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	3.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	5.7	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.3	—	ns	V <sub>DS</sub> = -30V, V <sub>GS</sub> = -10V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -5A
Turn-On Rise Time	t <sub>r</sub>	—	6.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	46.7	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	25.3	—	ns	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	13.6	—	ns	I <sub>f</sub> = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	7.4	—	nC	

- Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  8. Thermal resistance from junction to soldering point (on the exposed drain pad).
  9. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  10. Short duration pulse test used to minimize self-heating effect.
  11. Guaranteed by design. Not subject to product testing.



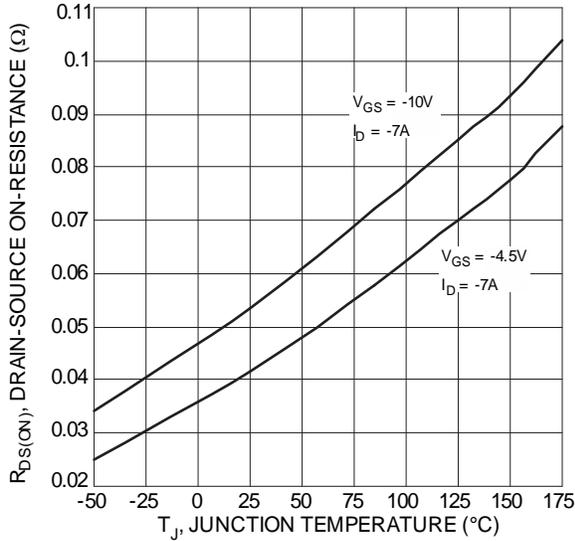


Figure 7 On-Resistance Variation with Temperature

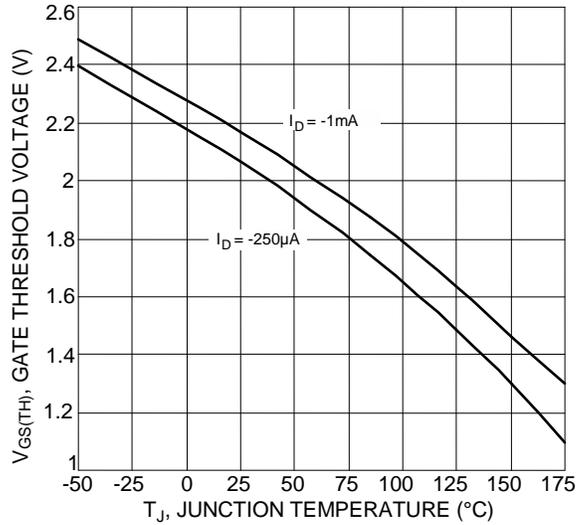


Figure 8 Gate Threshold Variation vs. Junction Temperature

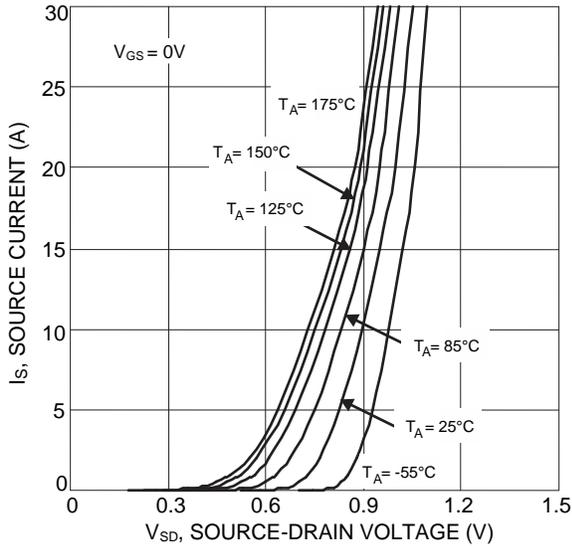


Figure 9 Diode Forward Voltage vs. Current

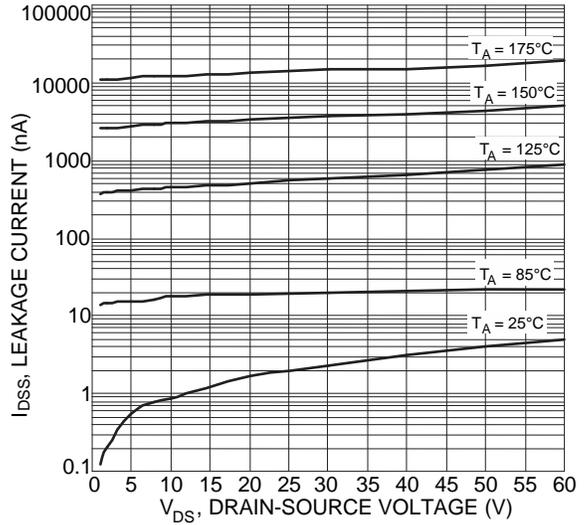


Figure 10 Typical Drain-Source Leakage Current vs. Voltage

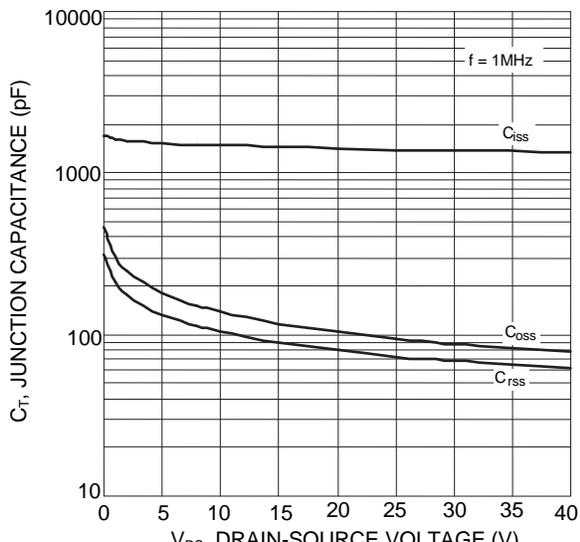


Figure 11 Typical Junction Capacitance

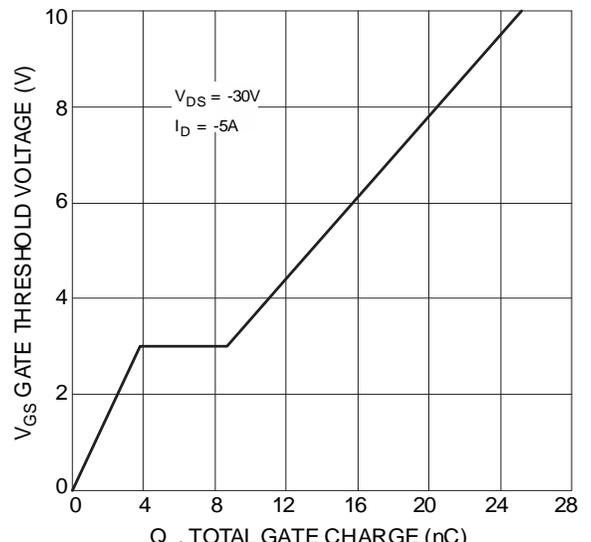
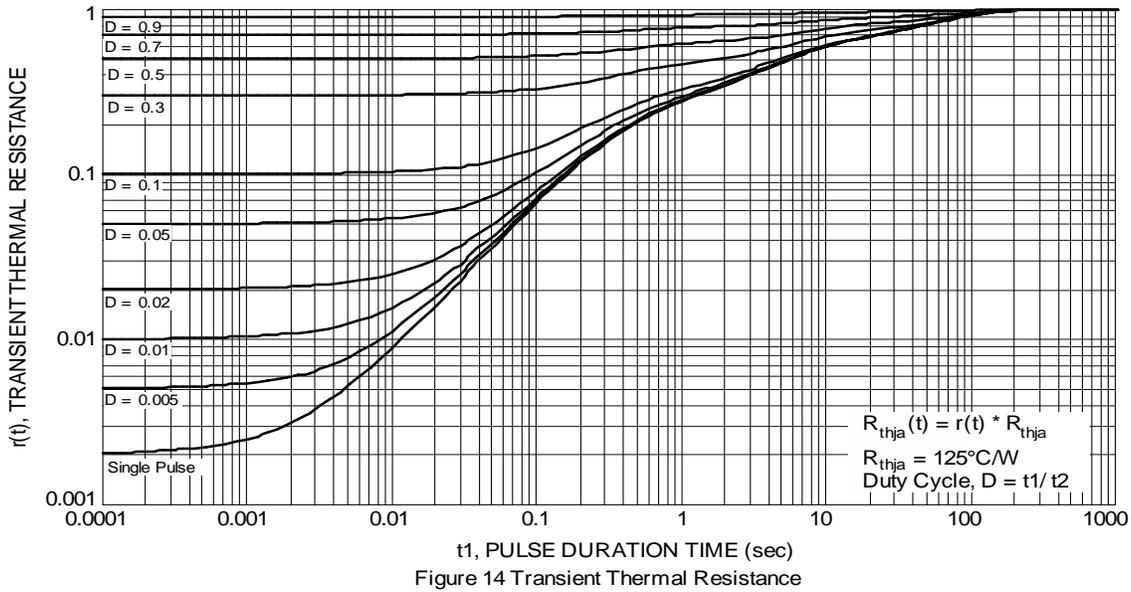
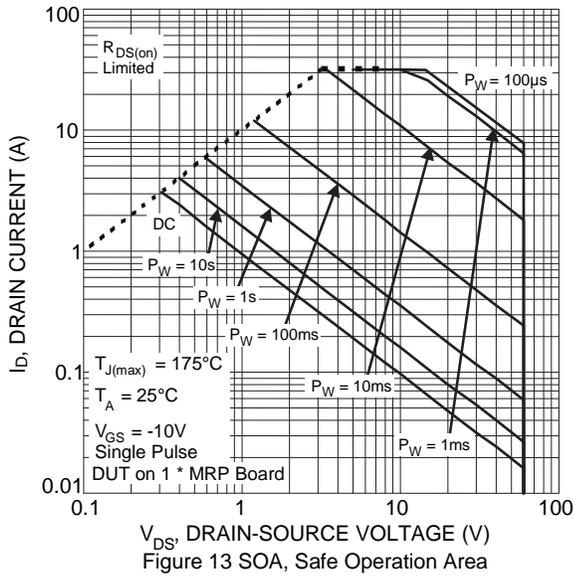


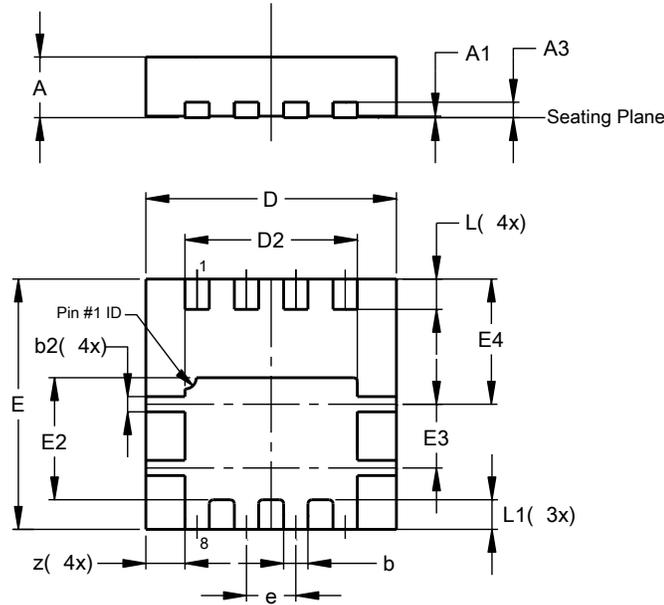
Figure 12 Gate Charge



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**

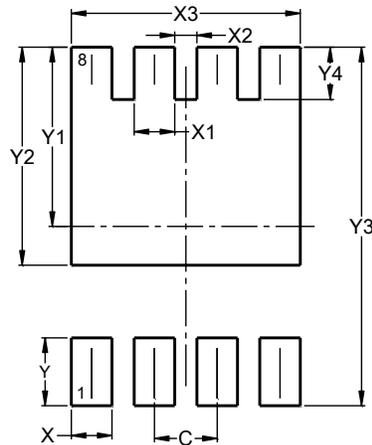


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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